

### GR-65P150AK: DFN 8x8 Cascode GaN HEMT

#### Description

GR-65P150AK is a normally-off GaN High electron mobility transistor (HEMT) device using the cascode configuration, which provides high breakdown voltage, high current and high operating speed which is suitable for high power applications.

#### Key Specifications

Part Number	GR-65P150AK
$V_{DSS}$	650V
$V_{(TR)DSS}$	800V
$R_{DS(ON)}$ , typ.	145m $\Omega$
$Q_G$ , typ.	8.6nC
Package	DFN 8 x 8 mm

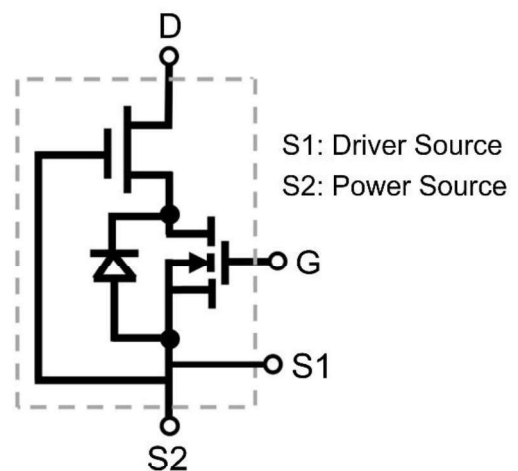


#### Features

- Gate drive voltage compatibility (-20V to +20V)
- High operating frequency
- Pin to Pin with CoolMOS/SJ and SiC MOSFET
- Low  $Q_{rr}$

#### Applications

- Switch Mode Power Supplies (SMPS)
- AC-DC/DC-DC Converters: Boost, Buck, QR Flyback, ACF, AHB, LLC, Half/Full Bridge Application
- Motor Drives, Lighting, Server



Cascode Device Structure